

56E D 3030609 0001110 972 VCT

查询VTS2076供应商

捷多邦, 专业PCB打样工厂

VTS-3 Process Photodiodes

VTS-76, 77 24小时加急出货

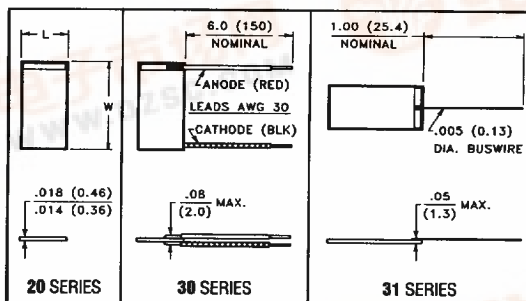
E G & G VACTEC

T-90-01

PRODUCT DESCRIPTION

Large area planar silicon photodiodes primarily intended for use in the photovoltaic mode. These devices have excellent response in the UV region and are designed for high output down to 220 nm. The cells have moderate shunt resistance and are optimized for use at lower light levels. These diodes have solderable contacts and are available with or without flexible leads. Devices with leads are acrylic (plastic) coated.

PACKAGE DIMENSIONS inch (mm)



CASE 448

ANODE (ACTIVE) SURFACE SHOWN
CATHODE IS BACKSIDE

ABSOLUTE MAXIMUM RATINGS

Storage Temperature:

-40°C to 150°C Series 20, 31

-40°C to 105°C Series 30

Operating Temperature:

-40°C to 125°C Series 20, 31

-40°C to 105°C Series 30

DIMENSIONS

VTS_76

VTS_77

L

.100 (2.54)

.087 (2.21)

W

.200 (5.08)

.200 (5.08)

ACTIVE AREA

.016² (10²).013² (8.5²)

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTS-3 curves, page 95)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTS_76			VTS_77						UNITS
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
I _{sc}	Short Circuit Current	H = 10 fc, 2850 K	6	7		5	6					μA
TC I _{sc}	I _{sc} Temp. Coefficient	2850 K		.18			.18					%/°C
I _{sc}	Short Circuit Current	40 mW/cm ² , 365 nm	.20	.65		.17	.55					μA
V _{oc}	Open Circuit Voltage	H = 10 fc, 2850 K		.20			.20					V
I _d	Dark Current	H = 0, V _R = 100 mV	100	400		100	400					nA
R _{SH}	Shunt Resistance	H = 0, V = 10 mV		.60			.60					MΩ
TC R _{SH}	R _{SH} Temp. Coefficient	H = 0, V = 10 mV		-11			-11					%/°C
C _J	Junction Capacitance	H = 0, V = 0 V		.10			.09					nF
λ _{range}	Spectral Application Range		220		1050	220		1050				nm
λ _p	Spectral Response - Peak			850			850					nm
SR	Sensitivity	@ Peak		.50			.50					A/W